

3MG2-P

SMART Definitions

Read Error Rate: 讀取錯誤率.

Reallocated Sectors Count: 當前備用磁區的總數, 會隨着壞磁區的替換逐漸減少.

Power On Hours: 上電時間(小時), 一般為 30000 小時.

Power Cycle Count: 上電次數.

Uncorrectable Sector Count On Line: 在讀取/寫入下, 無法校正磁區數.

Number of Pure Spare: 有效備用區塊數.

Number of Initial Block: 初始化無效區塊數.

Total Erase Count: 總共抹除數.

Max Erase Count: 最大抹除數.

Min Erase Count: 最小抹除數.

Average Erase Count: 平均抹除數.

Max Erase Count in Spec: 最大抹除數規格.

Remain Life Percentage: 剩餘壽命百分比($(P/E \text{ Cycle} - \text{Average Erase Count}) / P/E \text{ Cycle}$).

Worst Die Program Fail Count: 最差晶片中, 程序失敗次數.

Worst Die Erase Fail Count: 最差晶片中, 抹除失敗次數.

WearLeveling Count: 快閃記憶體抹寫次數.

Used Reserved Block Count: 使用保留區塊數.

Program Fail Count: 程序失敗次數.

Erase Fail Count: 抹除失敗次數.

Uncorrectable Error Count: 無法透過 ECC 修正的錯誤數量.

Power off Retract Count: 意外斷電次數.

Temperature: 設備溫度(-40 ~ 85).

Hardware ECC recovered: 每個磁區只要有 ECC, 次數會+1.

Reallocation Event Count: 無法校正錯誤次數.

Current pending sector count: 等待移動磁區數.

Uncorrectable Sector Count OffLine: 離線時, 無法校正總數.

UDMA CRC Error: **Device** 與 **Host** 之連接異常次數.

Available Reserved Space: 可用的留存空間.

Write Sector Count: 寫入磁區次數.

Read Sector Count: 讀取磁區次數.

Flash Write Count: 快閃記憶體寫入次數.